

pedestal bias. A greater pedestal bias will increase the energy with which the ionized metals impact the deposition surface. The present process preferably incorporates a pedestal bias configured to deposit metal atoms with sufficient force to sputter previously deposited metal and reduce or prevent the problems discussed above. This feature allows for sputtering away of excess material on the tapered sidewall portions, and thus helps to prevent shadowing of other cavity sidewall portions. In addition, the sputtered metal ions may impact with previously deposited metal at the bottom of the trench with sufficient energy to resputter, or "splash," that metal onto lower cavity sidewalls 208. The pedestal bias, however, is preferably not set so high as to sputter away too much of the deposited material from areas that receive the greatest amount of direct ion impact (e.g., tapered portions 210 of the cavity sidewall and cavity base 206). In particular, the pedestal bias is preferably set below a level that would result in thinning of the wetting layer upon the tapered portions of the cavity sidewalls.

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### **IN THE CLAIMS**

Please cancel non-elected claims 24-29 without prejudice or disclaimer as to the subject matter recited therein. Applicants reserve the right to file a divisional application at a later date capturing the subject matter recited in claims 24-29 canceled herein.

### **REMARKS**

The Specification has been amended to correct grammatical errors and, therefore, the amendment does not present new matter. In addition, non-elected claims 24-29 have been canceled. Thus, claims 1-18 and 22, 23, and 30 are currently pending in the case. Further examination and reconsideration of the presently claimed application is respectfully requested.

### **Allowable Claims**

Allowance of claims 12-18, 22, and 23 is gratefully acknowledged.